

## Supplementary Information

### Experimental

#### *Synthesis of HfO<sub>2</sub> and ZrO<sub>2</sub> based Nanoparticles*

The HfO<sub>2</sub> and ZrO<sub>2</sub> based nanoparticles were synthesized by the modified sol-gel method as reported previously.<sup>[1]</sup> A fixed amount of hafnium isopropoxide (Aldrich, 99.9%) (or zirconium isopropoxide for the synthesis of ZrO<sub>2</sub> nanoparticles) was firstly dissolved into 30 mL methacrylic acid (MAA, Sigma Aldrich, 99%) and was stirred at 65 °C for 5-10 minutes to obtain a clear solution. A solution composed of 9 mL methacrylic acid and 1 mL water was added dropwise into the precursor solution. The mixture was then aged at 65 °C for 18 hours. The white precipitate was centrifuged and collected after washing with water and acetone multiple times. The final product HfO<sub>2</sub>/MAA (denoted as HfMAA) was obtained after overnight drying in the vacuum oven at 60°C and stored for further use. HfO<sub>2</sub>/trans-2,3-dimethylacrylate (denoted as HfDMA), HfO<sub>2</sub>/2-methylbutric acid (denoted as Hf2MBA), HfO<sub>2</sub>/isobutyric acid (denoted as HfIBA) were synthesized with the same procedure with the corresponding acids replacing methacrylic acid. ZrO<sub>2</sub> based nanoparticles were synthesized using a similar procedure.

#### *Solubility Tests*

25 mg of the appropriate nanoparticle system and a fixed amount of photoacid generator (PAG) N-hydroxynaphthalimidetriplate (1 and 5 wt%, respectively) were dissolved into propylene glycol monomethyl ether acetate (PGMEA, Sigma-Aldrich, 99.5%) with a total mass up to 250 mg. The solution was filtered with a 0.2 μm syringe filter to remove large particles and was then spin-coated on pre-cleaned silicon wafers (WRS materials) at 2000 rpm for 60 seconds. The thickness of the deposited photoresist film was about 100 nm. The film was heated at 110 °C for 60s to remove excess solvent and then exposed to 254 nm wavelength deep UV light with a dosage of 150 mJ/cm<sup>2</sup> through a quartz mask. An ABM mask aligner was used for photo-patterning. The silicon wafers before and after exposure were cut into 5 mm×5 mm pieces and were immersed into 5 mL of different solvents for solubility testing.

#### *Materials Characterization*

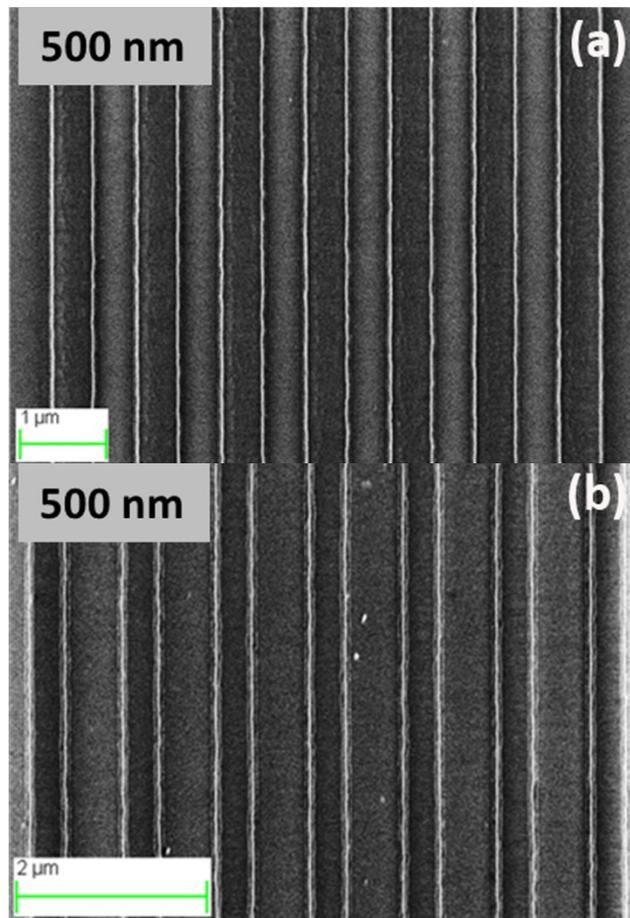
Infrared spectra were collected by attenuated total reflectance with a Nicolet iZ10 ATR-FTIR spectrometer. 64 scans with 4 cm<sup>-1</sup> resolution were used for analysis. Thermogravimetric analysis and differential thermal analysis (TG/DTA) were performed with a Seiko Instruments TD/DTA 6200. The thermal analysis was conducted under N<sub>2</sub> atmosphere with a heating rate of 10 °C/min from room temperature to 580°C. Particle size and particle size distribution were obtained with the Malvern Zetasizer. Scanning electron microscopy images were collected on Zeiss LEO 1550 FE-SEM with an accelerating voltage of 1 kV.

**Table S1.** Weight percentage of different hybrid nanoparticles after heating from room temperature to 580 °C with a heating rate of 10°C/min.

<b>Materials</b>	<b>HfO<sub>2</sub></b>				<b>ZrO<sub>2</sub></b>			
	MAA	tDMA	2MBA	IBA	MAA	tDMA	2MBA	IBA
<b>Weight (%)</b>	59	64	51	64	62	54	47	49

**Table S2.** The Hansen solubility parameters and dielectric constant ( $\epsilon$ ) of solvents used for the solubility test and the corresponding parameters for the hybrid nanoparticles.

Solvent	$\delta_d$ (MPa <sup>1/2</sup> )	$\delta_p$ (MPa <sup>1/2</sup> )	$\delta_h$ (MPa <sup>1/2</sup> )	$\epsilon$
Water	15.6	16	42.3	80.1
Methanol	15.1	12.3	22.3	32.4
Acetonitrile	15.3	18	6.1	37.5
Isopropyl alcohol	15.8	6.1	16.4	19.92
Dimethylformamide	17.4	13.7	11.3	37.1
Acetone	15.5	10.4	7	20.7
Methyl ethyl ketone	16	9	5.1	18.5
Ethyl acetate	15.8	5.3	7.2	6.02
4-methyl-2-pentanol	15.4	3.3	12.3	10.4
PGMEA	16.1	6.1	6.6	8.3
Methyl isobutyl ketone	15.3	6.1	4.1	13.11
n-butyl acetate	15.8	3.7	6.3	5.01
Methylenechloride	18.2	6.3	6.1	9.1
Chloroform	17.8	3.1	5.7	4.8
Chlorobenzene	19	4.3	2	5.62
Toluene	18	1.4	2	2.24
Decalin	18.4	0	0	2.2
<b>Hybrid Nanoparticles</b>				
ZrMAA	16.6	8.6	12.2	-
HfDMA	16.7	8.5	11.1	-
ZrDMA	16.7	8.5	11.1	-
HfIBA	18.4	8.5	4.6	-
ZrIBA	20.0	7.7	10.3	-
Hf2MBA	21.1	7.6	9.2	-
Zr2MBA	21.1	7.6	9.2	-



**Figure S1.** SEM images of photo-patterns by 254 nm deep UV lithography from (a) ZrMMA and (b) HfMMA with addition of 1 wt% PAG in 4-methyl-2-pentanol developer.

#### **Reference**

- [1] L. Li, S. Chakrabarty, K. Spyrou, C. K. Ober, E. P. Giannelis, *Chem. Mater.* 2015, 27, 5027.